

WAFER MANUFACTURING METHOD

ABSTRACT

A wafer manufacturing method includes a first peel-off layer forming step of forming a first peel-off layer in an ingot by applying a laser beam having a wavelength transmittable through the ingot while positioning a focused spot of the laser beam in the ingot at a first depth from an end face of the ingot for fabricating a larger-diameter wafer, a second peel-off layer forming step of forming a second peel-off layer in the ingot for fabricating a smaller-diameter wafer by applying the laser beam to an area of the ingot that is smaller in diameter than the ingot while positioning the focused spot in the ingot at a second depth, which is smaller than the first depth, from the end face of the ingot, and a separating wall forming step of forming an annular first separating wall along an outer circumferential edge of the smaller-diameter wafer by applying the laser beam to the ingot while positioning the focused spot on an annular area extending from the end face of the ingot to the second peel-off layer.

[FIG. 4A]